



SMPS MOSFET

PD - 93934B

IRFR3707
IRFU3707

Applications

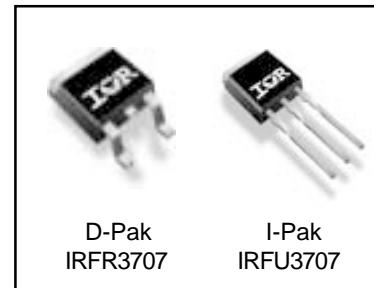
- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial use
- High Frequency Buck Converters for Computer Processor Power

HEXFET® Power MOSFET

V_{DSS}	R_{DS(on)} max	I_D
30V	13mΩ	61A ^④

Benefits

- Ultra-Low R_{DS(on)}
- Very Low Gate Impedance
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-to-Source Voltage	± 20	V
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	61 ④	
I _D @ T _C = 70°C	Continuous Drain Current, V _{GS} @ 10V	51 ④	A
I _{DM}	Pulsed Drain Current①	244	
P _D @ T _C = 25°C	Maximum Power Dissipation③	87	W
P _D @ T _C = 70°C	Maximum Power Dissipation③	61	W
	Linear Derating Factor	0.59	mW/°C
T _J , T _{STG}	Junction and Storage Temperature Range	-55 to + 175	°C

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	1.73	°C/W
R _{θJA}	Junction-to-Ambient (PCB mount)*	—	50	
R _{θJA}	Junction-to-Ambient	—	110	

* When mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ④ are on page 9

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(\text{BR})\text{DSS}}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu\text{A}$
$\Delta V_{(\text{BR})\text{DSS}/\Delta T_J}$	Breakdown Voltage Temp. Coefficient	—	0.027	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(\text{on})}$	Static Drain-to-Source On-Resistance	—	9.7	13	$\text{m}\Omega$	$V_{GS} = 10V, I_D = 15\text{A}$ ③
		—	13.2	17.5		$V_{GS} = 4.5V, I_D = 12\text{A}$ ③
$V_{GS(\text{th})}$	Gate Threshold Voltage	1.0	—	3.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$

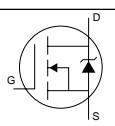
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_f	Forward Transconductance	37	—	—	S	$V_{DS} = 15V, I_D = 49.6\text{A}$
Q_g	Total Gate Charge	—	19	—	nC	$I_D = 24.8\text{A}$
Q_{gs}	Gate-to-Source Charge	—	8.2	—		$V_{DS} = 15V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.3	—		$V_{GS} = 4.5V$ ③
Q_{oss}	Output Gate Charge	—	18	27		$V_{GS} = 0V, V_{DS} = 15V$
$t_{d(\text{on})}$	Turn-On Delay Time	—	8.5	—	ns	$V_{DD} = 15V$
t_r	Rise Time	—	78	—		$I_D = 24.8\text{A}$
$t_{d(\text{off})}$	Turn-Off Delay Time	—	11.8	—		$R_G = 1.8\Omega$
t_f	Fall Time	—	3.3	—		$V_{GS} = 4.5V$ ③
C_{iss}	Input Capacitance	—	1990	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	707	—		$V_{DS} = 15V$
C_{rss}	Reverse Transfer Capacitance	—	50	—		$f = 1.0\text{MHz}$

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	213	mJ
I_{AR}	Avalanche Current①	—	61	A

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_s	Continuous Source Current (Body Diode)	—	—	61④	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	244		
V_{SD}	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 31\text{A}, V_{GS} = 0V$ ③
		—	0.8	—		$T_J = 125^\circ\text{C}, I_S = 31\text{A}, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	39	59	ns	$T_J = 25^\circ\text{C}, I_F = 31\text{A}, V_R=20V$
Q_{rr}	Reverse Recovery Charge	—	49	74	nC	$dI/dt = 100\text{A}/\mu\text{s}$ ③
t_{rr}	Reverse Recovery Time	—	42	63	ns	$T_J = 125^\circ\text{C}, I_F = 31\text{A}, V_R=20V$
Q_{rr}	Reverse Recovery Charge	—	62	93	nC	$dI/dt = 100\text{A}/\mu\text{s}$ ③

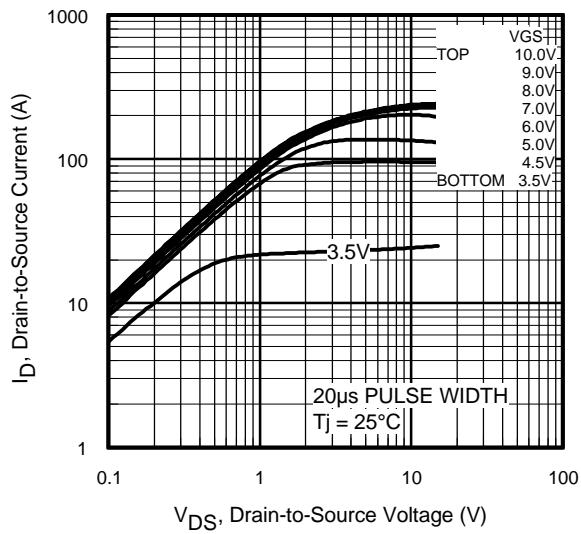


Fig 1. Typical Output Characteristics

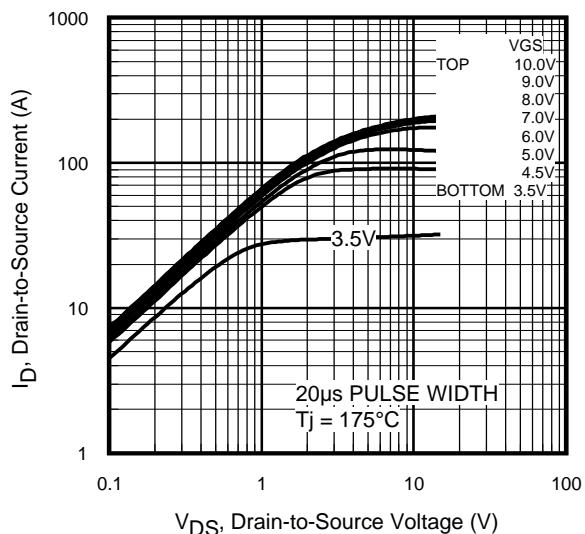


Fig 2. Typical Output Characteristics

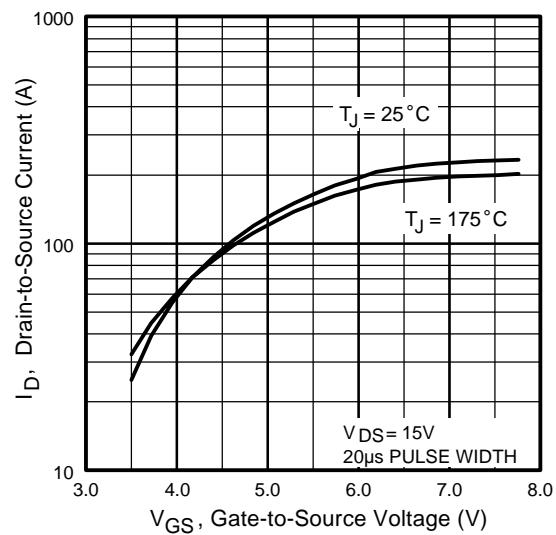


Fig 3. Typical Transfer Characteristics

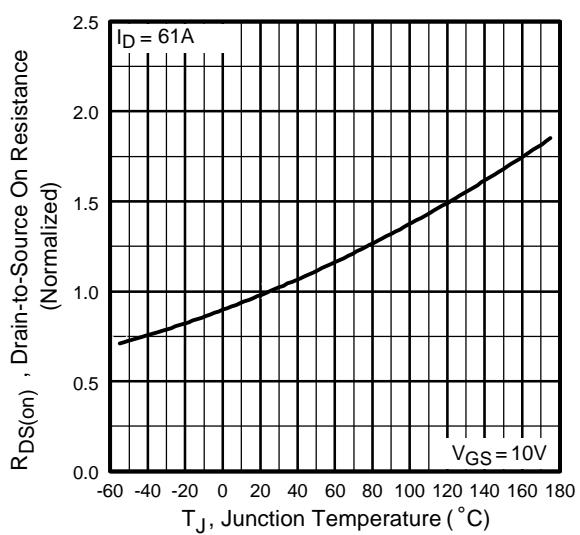


Fig 4. Normalized On-Resistance
Vs. Temperature

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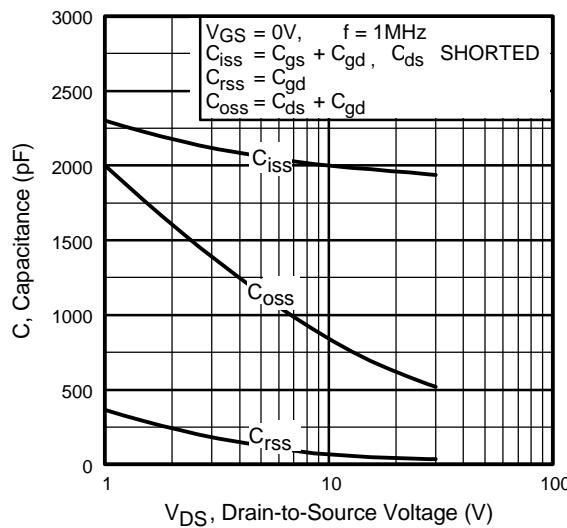


Fig 5. Typical Capacitance Vs.
Drain-to-Source Voltage

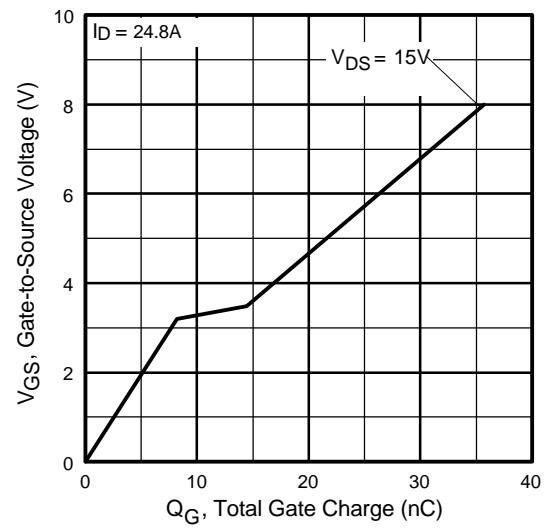


Fig 6. Typical Gate Charge Vs.
Gate-to-Source Voltage

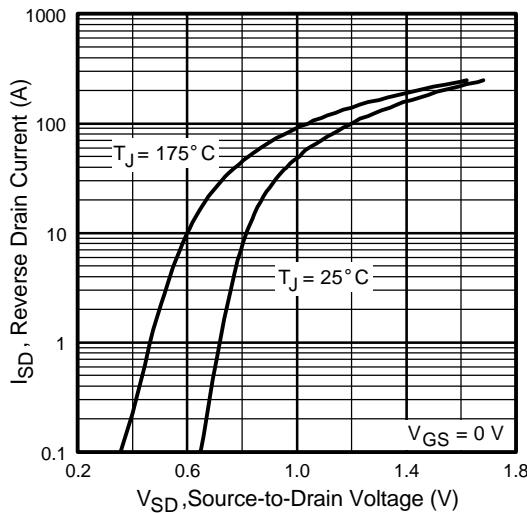


Fig 7. Typical Source-Drain Diode
Forward Voltage

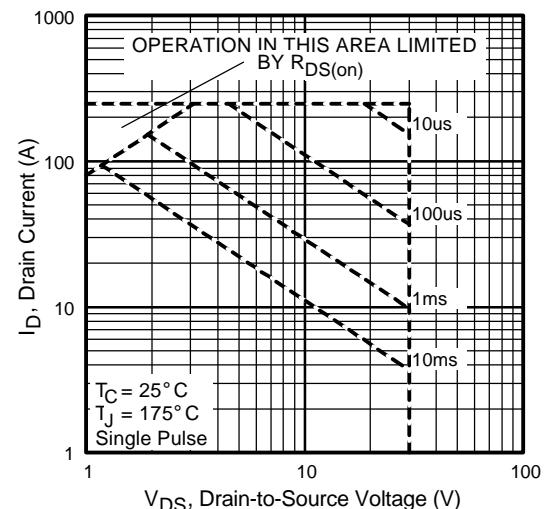


Fig 8. Maximum Safe Operating Area

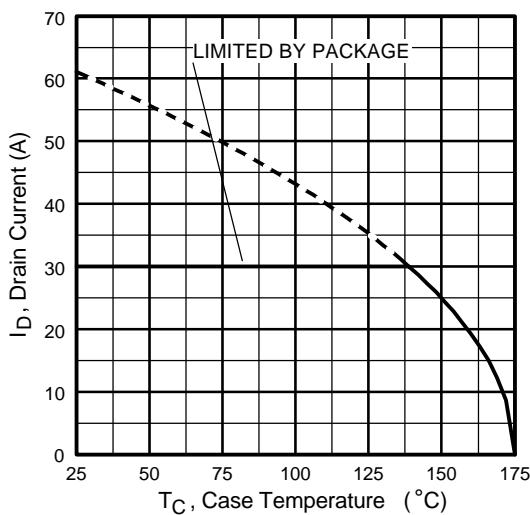


Fig 9. Maximum Drain Current Vs.
Case Temperature

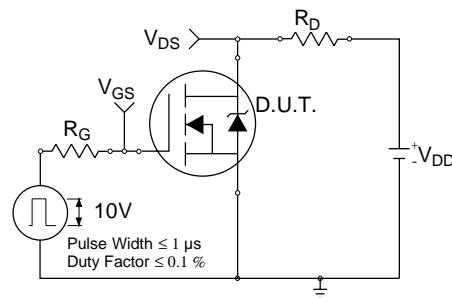


Fig 10a. Switching Time Test Circuit

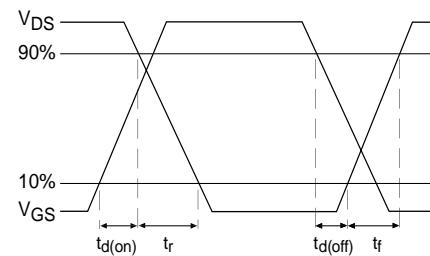


Fig 10b. Switching Time Waveforms

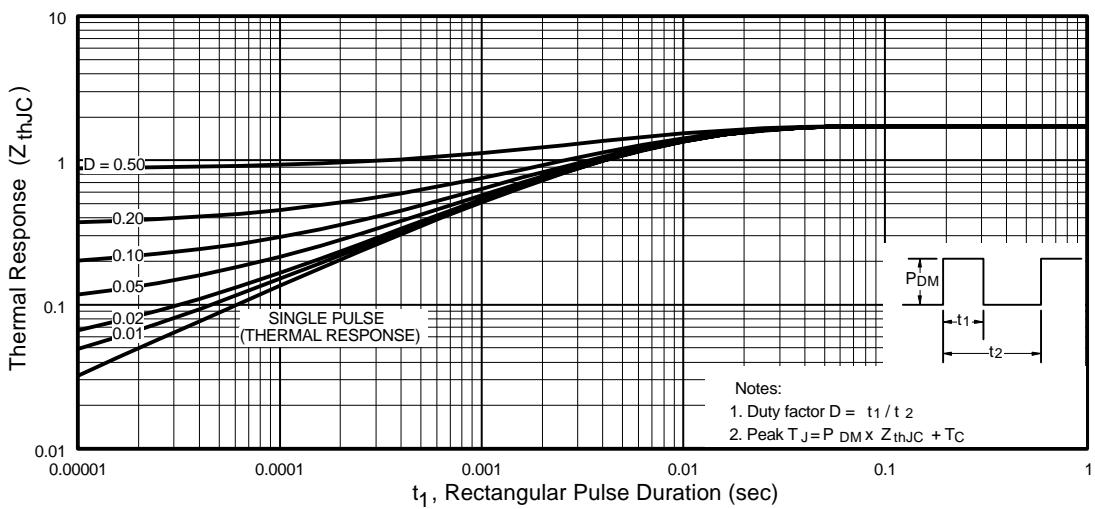


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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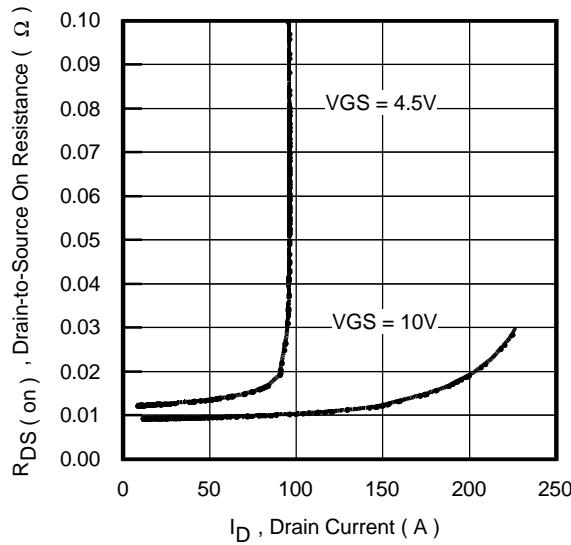


Fig 12. On-Resistance Vs. Drain Current

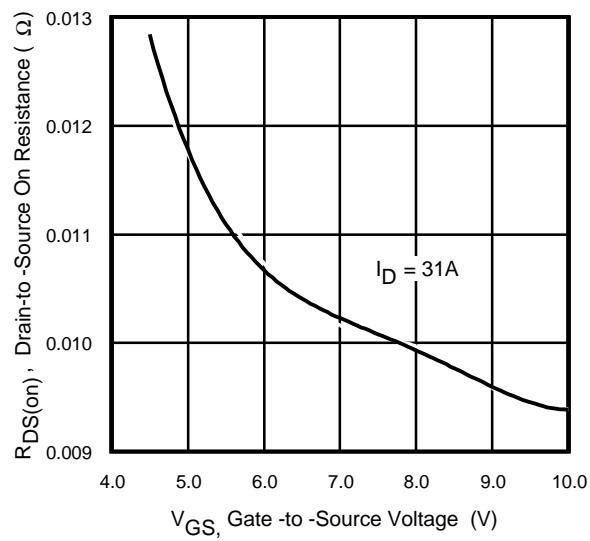


Fig 13. On-Resistance Vs. Gate Voltage

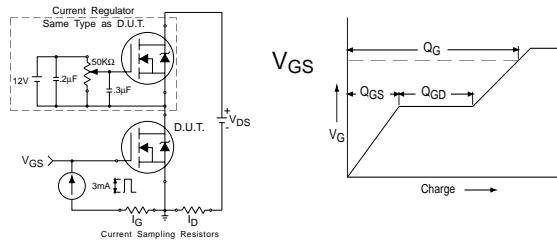


Fig 14a&b. Basic Gate Charge Test Circuit and Waveforms

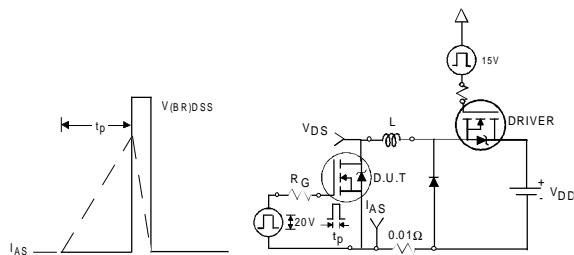


Fig 15a&b. Unclamped Inductive Test Circuit and Waveforms

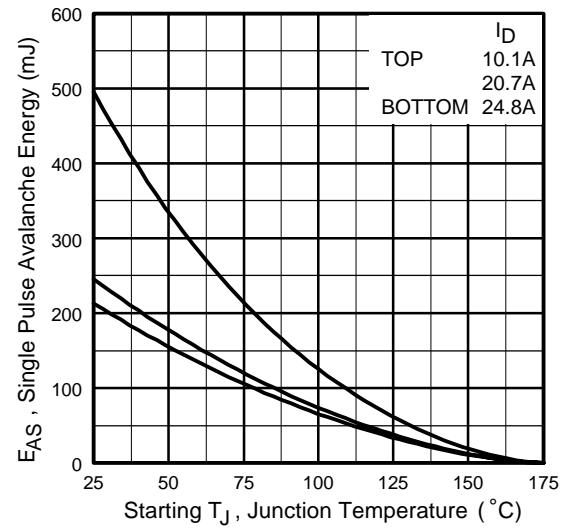
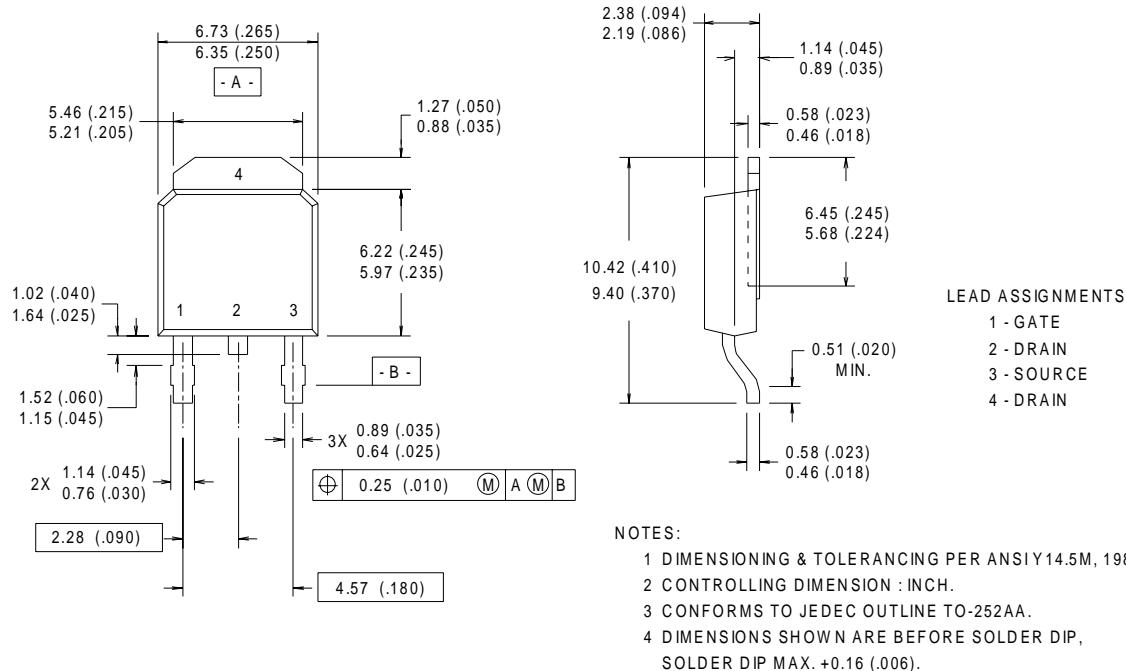


Fig 15c. Maximum Avalanche Energy Vs. Drain Current

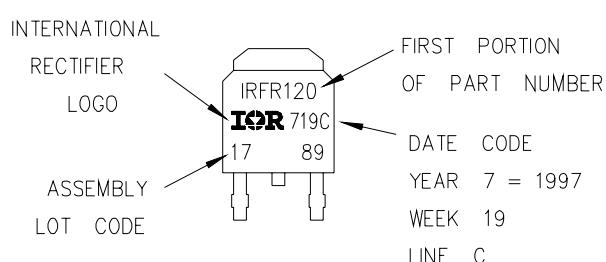
D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

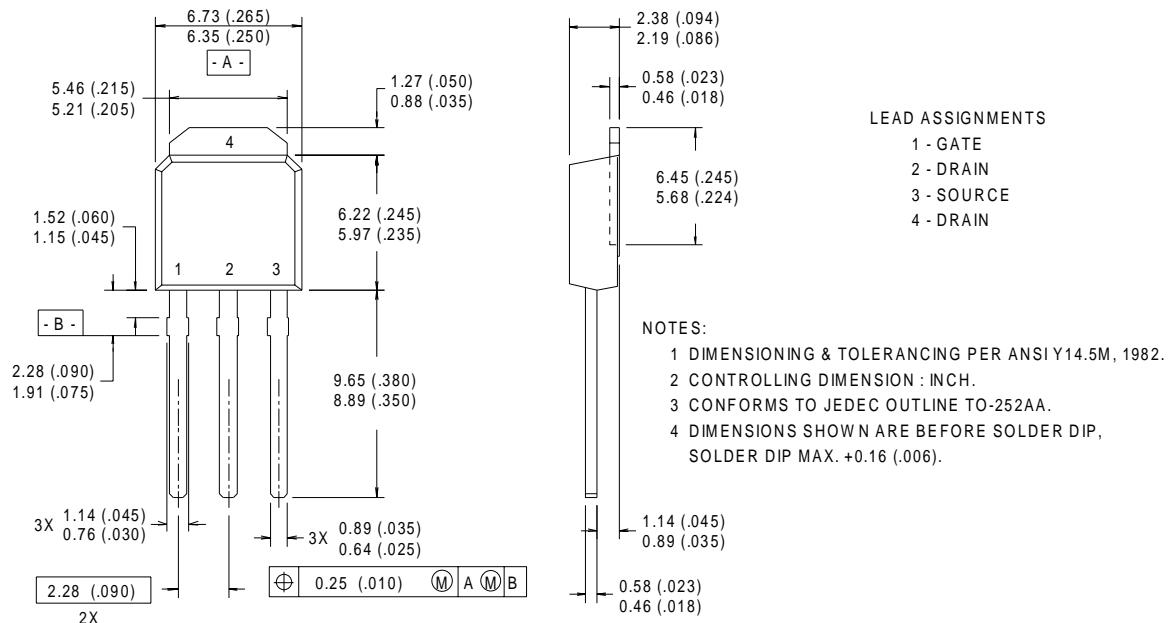


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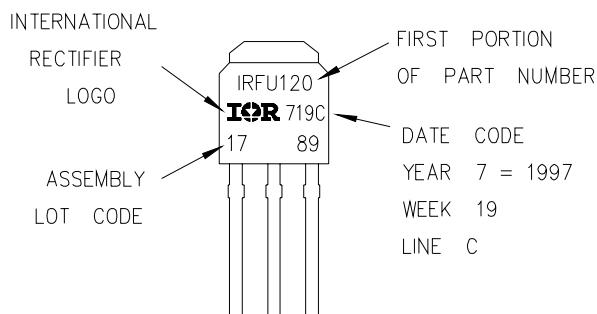
I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



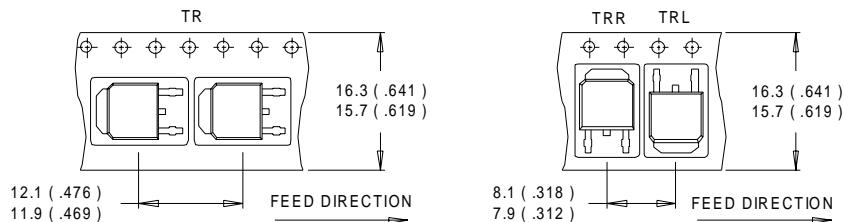
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE "C"



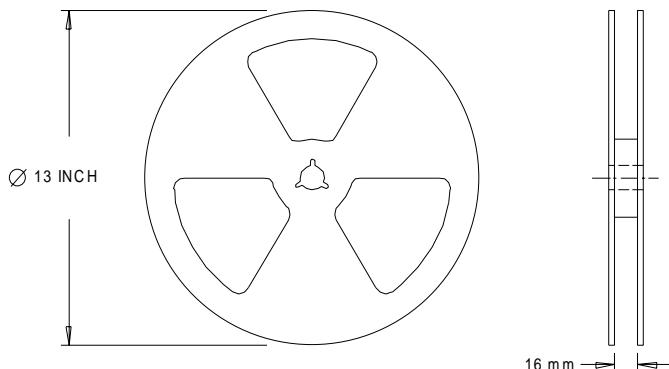
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Notes:

- | | |
|--|--|
| ① Repetitive rating; pulse width limited by max. junction temperature. | ③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$. |
| ② Starting $T_J = 25^\circ C$, $L = 0.7 \text{ mH}$
$R_G = 25\Omega$, $I_{AS} = 24.8 \text{ A}$. | ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A |

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IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111

IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630

IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936

Data and specifications subject to change without notice. 8/00

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>